IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 09/652,550
Priority Filing Date ..... August 31, 2000
Inventor ..... Keiji Jono et al.
Assignee ..... Micron Technology, Inc. and KMT Semiconductor, LTD
Priority Group Art Unit 2811
Priority Examiner ..... T. Tran
Attorney's Docket No. KM1-003
Title: Methods of Forming an Isolation Trench in a Semiconductor, Methods of Forming an Isolation Trench in a Surface of a Silicon Wafer, Methods of Forming an Isolation Trench-Isolated Transistor, Trench-Isolated Transistor, Trench Isolation Structures Formed in a Semiconductor, Memory Cells and DRAMS

PRELIMINARY AMENDMENT

To: Assistant Commissioner for Patents
Washington, D.C. 20231

From: Frederick M. Fliegel, Ph.D.
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Sir:

This is a preliminary amendment accompanying a Request for Divisional Application for the above-entitled patent application. Prior to examining the application, please enter the following amendments.

AMENDMENTS